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March 2013

FQT5P10

P-Channel QFET® MOSFET

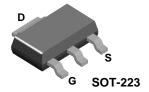
-100 V, -1.0 A, 1.05 Ω

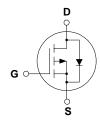
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -1.0 A, -100 V, $R_{DS(on)}$ =1.05 $\Omega(Max.)$ @ V_{GS} =-10 V, I_D =-0.5 A
- Low Gate Charge (Typ. 6.3 nC)
- Low Crss (Typ. 18 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQT5P10	Unit	
V _{DSS}	Drain-Source Voltage		-100	V	
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 70°C)		-1.0	А	
			-0.8	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	-4.0	А	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	55	mJ	
I _{AR}	Avalanche Current	(Note 1)	-1.0	А	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	0.2	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-6.0	V/ns	
P_D	Power Dissipation (T _C = 25°C)		2.0	W	
	- Derate above 25°C		0.016	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	Тур	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *		62.5	°C/W

^{*} When mounted on the minimum pad size recommended (PCB Mount)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_D = -250 \mu\text{A}$	-100			V
ΔB _{VDSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I _D = -250 μA, Referenced to 25°C		-0.1		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -100 V, V _{GS} = 0 V			-1	μΑ
		V _{DS} = -80 V, T _C = 125°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -0.5 A		0.82	1.05	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_D = -0.5 \text{ A}$ (Note 4)		1.4		S
Dynam C _{iss}	ic Characteristics Input Capacitance	V _{DS} = -25 V, V _{GS} = 0 V,		190	250	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		70	90	pF
C _{rss}	Reverse Transfer Capacitance			18	25	pF
Switchi	ng Characteristics		•			
t _{d(on)}	Turn-On Delay Time	V 50 V I 45 A		9	30	ns
t _r	Turn-On Rise Time	$V_{DD} = -50 \text{ V}, I_{D} = -4.5 \text{ A},$ $R_{G} = 25 \Omega$		70	150	ns
t _{d(off)}	Turn-Off Delay Time	NG - 20 32		12	35	ns
t _f	Turn-Off Fall Time	(Note 4, 5		30	70	ns
Qg	Total Gate Charge	$V_{DS} = -80 \text{ V}, I_{D} = -4.5 \text{ A},$		6.3	8.2	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		1.7		nC
Q _{gd}	Gate-Drain Charge	(Note 4, 5		3.0		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-1.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	orward Current			-4.0	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -1.0 \text{ A}$			-4.0	V
trr	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = -4.5 \text{ A,}$		85		ns
Qrr	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$ (Note 4)		0.27		μC

- Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 83mH, I_{AS} = -1.0A, V_{DD} = -25V, R_G = 25 Ω . Starting T_J = 25°C 3. I_{SD} ≤ -4.5A, di/dt ≤ 300A/ μ s, V_{DD} ≤ BV $_{DSS}$, Starting T_J = 25°C 4. Pulse Test : Pulse width ≤ 300 μ s, Duty cycle ≤ 2% 5. Essentially independent of operating temperature

Typical Characteristics

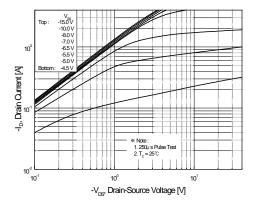


Figure 1. On-Region Characteristics

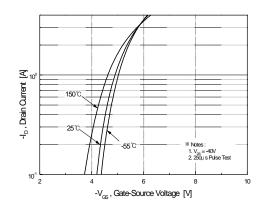


Figure 2. Transfer Characteristics

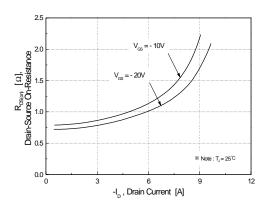


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

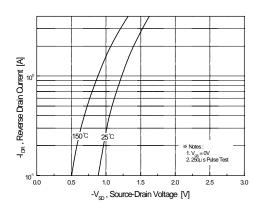


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

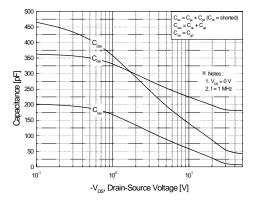


Figure 5. Capacitance Characteristics

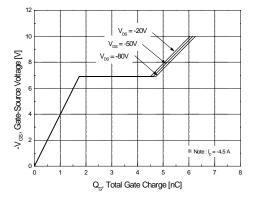
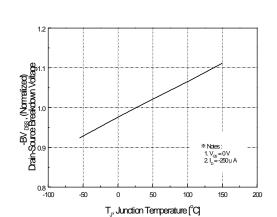


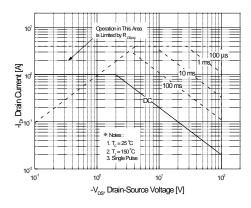
Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



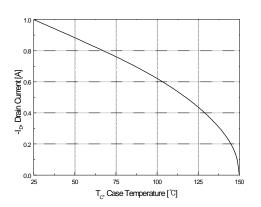


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

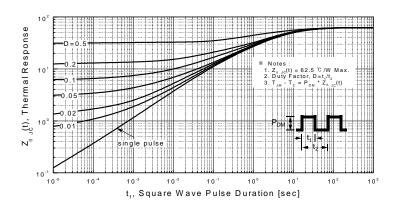
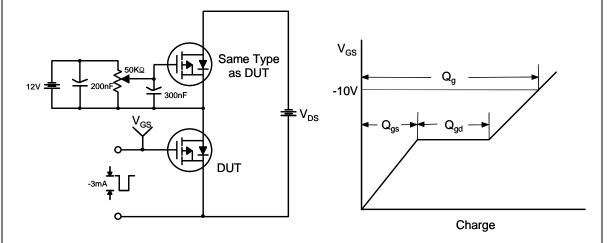
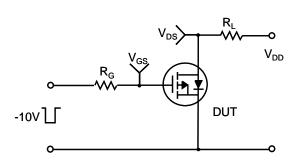


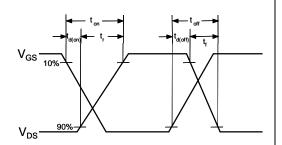
Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform

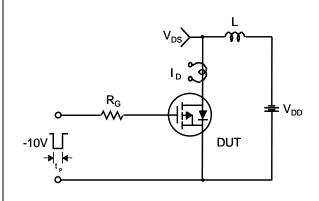


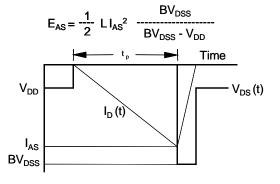
Resistive Switching Test Circuit & Waveforms



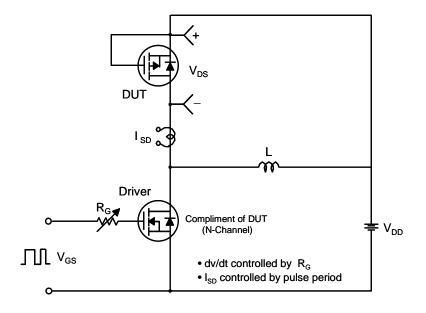


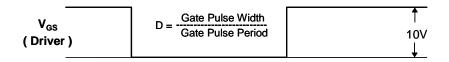
Unclamped Inductive Switching Test Circuit & Waveforms

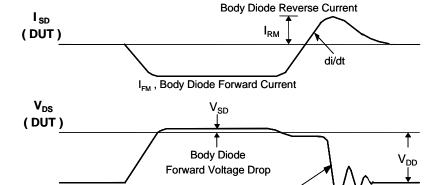




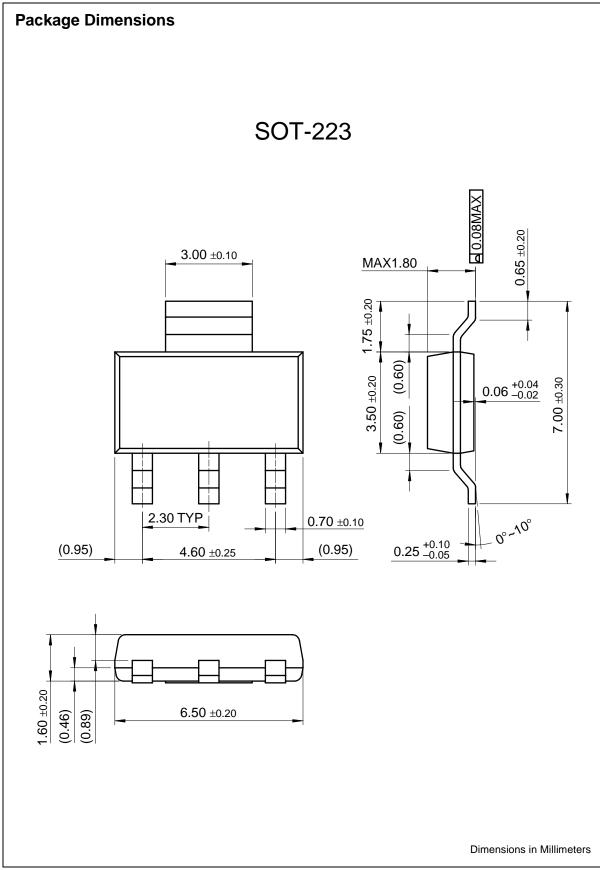
Peak Diode Recovery dv/dt Test Circuit & Waveforms







Body Diode Recovery dv/dt







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